

Amendments to the Specification

Please replace the paragraph on page 3, line 18 with the following amended paragraph:

The object is attained by using the recording film material for, as a phase change film of the nonvolatile memory, recording information by causing a reversible phase change between a crystal phase and an amorphous phase, the material including (1) a finite amount of at least one element selected from the group consisting of Ge and Sb, ~~and~~ (2) Te of 40 atom percent or more, and (3) at least one element selected from the elements in a 2b group, 1b group, 3a to 7a groups and an 8 group of 20 atom percent to 50 atom percent.